

Description

US5S204 is a widely used, low-jitter, low-power clock sector output buffer. It can allocate one of two inputs to four low-jitter LVCMOS clock outputs. Its can adopt differential or single-ended signals inputs. This buffer is suitable for various mobile and wired infrastructure, data communication, computing, low-power medical imaging and portable test and measurement applications. The core voltage of the device supports 2.5 V or 3.3 V, and the output voltage supports 1.5 V, 1.8 V, 2.5 V or 3.3 V.

Applications

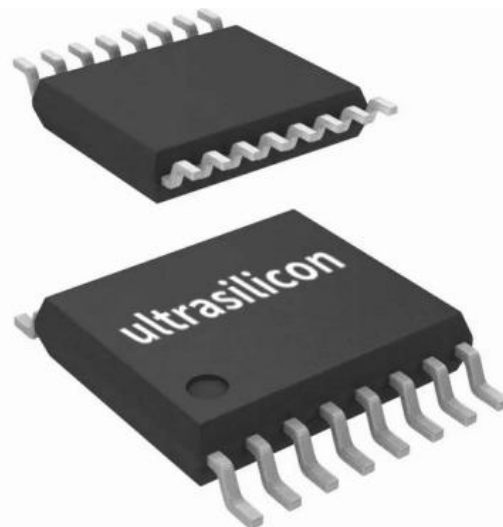
- General-Purpose Communication, Industrial, and Consumer Applications

Device Information

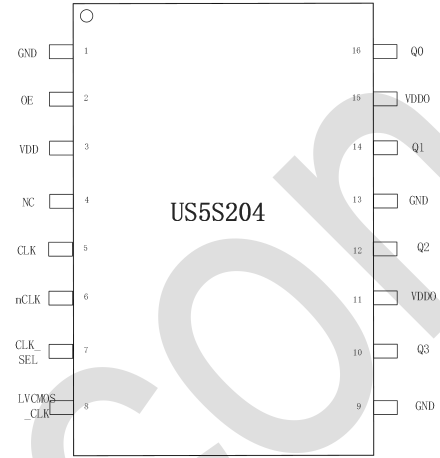
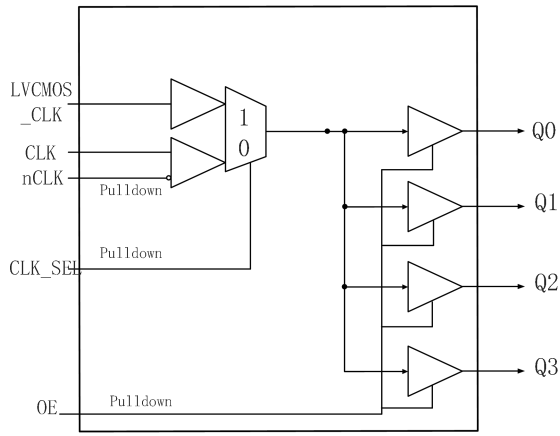
Part Number	Package	Body Size(NOM)
US5S204	TSSOP-16	5.00mm x 4.40mm

Features

- High-Performance 2:4 LVCMOS Clock Buffer
- Output Skew < 50 ps (Typical 3.3V)
- Transmission delay : 1.5 ns (Typical)
- Maximum operating frequency : 250MHz(VDDO=3.3V)
- Input supports LVPECL, LVDS, HCSL, SSTL or LVCMOS signal
- Differential and single terminal support 250MHz
- Supply voltage(VDD/VDDO):
3.3V/3.3V, 2.5V,1.8V,1.5V
2.5V/2.5V,1.8V,1.5V
- Additive RMS phase jitter @ 156.25MHz:
< 100 fs RMS (10kHz - 20MHz)
- Industrial Temperature Range: -40°C to 85°C
- Available in 16-Pin TSSOP Package



Block Diagram



Pin Description and Function Table

管脚号	管脚名称	管脚类型	说明
1	GND	Power	Ground.
2	OE	Input	Output enable input. 0 = Outputs in Hi-Z state 1 = Outputs in active state.
3	VDD	Power	Power supply.
4	NC	NC	NC.
5	CLK	Input	Non-inverting differential clock input 0.
6	nCLK	Input	Inverting differential clock input 0. Internally biased to VDD/2 when left floating.
7	CLK_SEL	Input	Clock select input. 0 = Select CLK, nCLK 1 = Select LVCMOS_CLK.
8	LVCMOS_CLK	Input	Single-ended clock input.
9	GND	Power	Ground.
10	Q3	Output	Single-ended clock outputs 3.
11	VDDO	Power	Output supply pin.
12	Q2	Output	Single-ended clock outputs 2.
13	GND	Power	Ground.
14	Q1	Output	Single-ended clock outputs 1.
15	VDDO	Power	Output supply pin.
16	Q0	Output	Single-ended clock outputs 0.

Input logic

CLK_SEL	输入选择
0	CLK,nCLK
1	LVCMOS_CLK

OE Control Table

OE	Qx
0	Hiz
1	Enable

Absolute Maximum Ratings

Exposure to absolute maximum rating conditions for extended periods may affect product reliability. Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of the product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied.

Item	Rating
V _{DD} : Supply voltage	-0.5V to 4.6V
V _{IN} : Input voltage	-0.5V to V _{DD} + 0.5 V
V _{OUT} : Output voltage	
T _{STG} :Storage Temperature	-65°C to 150°C

ESD Ratings

		Max	Unit
V(ESD) Electrostatic discharge	Human-body model (HBM), ANSI/ESDA/JEDEC JS-001-2017	±2500	V
	Machine model (MM), JEDEC Std. JESD22-A115-C	±250	
	Charged-device model (CDM), ANSI/ESDA/JEDEC JS-002-2018	±750	

Latch up

		Max	Unit
Latch up	I-test, JEDEC STD JESD78E	±200	mA
	V-test, JEDEC STD JESD78E	4.6	V

Recommended Operating Conditions

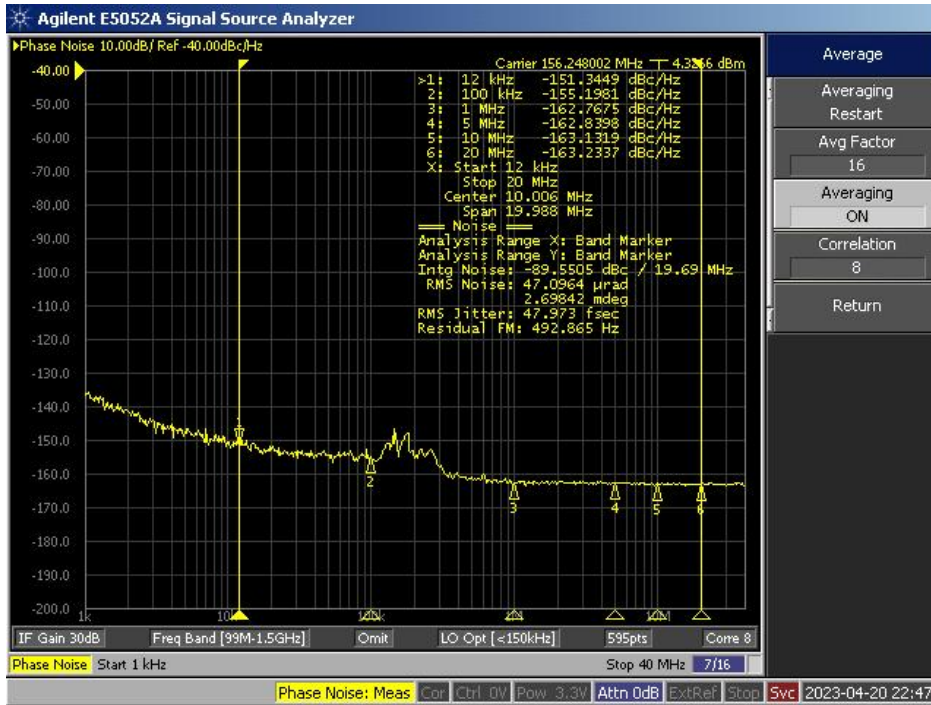
Symbol	Parameter	Min	Typ	Max	Unit
T _A	Ambient air temperature	-40	-	85	°C
T _J	Junction temperature		-	125	°C
V _{DD}	Power supply for Core and input Buffer blocks	3.3-5% 2.5-5%	3.3 2.5	3.3+5% 2.5+5%	V
V _{DDO}	output voltage	3.3-5% 2.5-5% 1.8-5% 1.5-5%	3.3 2.5 1.8 1.5	3.3+5% 2.5+5% 1.8+5% 1.5+5%	V

Electrical Characteristics

VDD = 3.3 V ± 5 %, -40°C ≤ TA ≤ 85°C. Typical values are at VDD = 3.3 V, 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input characteristics					
INPUT					
I _{DD_LVCMOS}	Core supply current	Power Supply Current through VDD, VDDO, 10MHz		8.6	mA
I _{DD_Differential}	Core supply current	Power Supply Current through VDD, VDDO, 10MHz		9.3	mA
f _{CLKin}	Input frequency		0.1	250	MHz
V _{IHD}	Input high voltage	Differential input	VDD		V
V _{ILD}	Input low voltage		GND		V
V _{ID}	Differential input voltage swing		0.15	1.3	V
V _{CMD}	Differential input common mode voltage		0.5 0.85	VDD -	V
V _{IH}	Single-ended input high-level voltage	Single-ended input (DC or AC coupling)	VDD		V
V _{IL}	Single-end input low-level voltage		GND		V
V _{I_SE}	Single-end input voltage swing		0.3	2	V
V _{CM}	Single-ended input common mode voltage		0.25 1.2	VDD -	
LVC MOS output characteristics					
f _{OUT}	Maximum output frequency		0.1	250	MHz
Jitter _{ADD}	Additional jitter (12KHz-20MHz)	CLKin: 156.25 MHz, LVC MOS Input CLKin: 156.25 MHz, Differential Input	65 36		fs
Duty Cycle	Duty Cycle		45%	55%	
V _{OH}	High voltage output	I _{OH} = -8 mA	2.6		V
V _{OL}	Low voltage output	I _{OH} = 8 mA		0.5	V
t _R	Output rise time (20% TO 80%)		0.32	0.8	ns
t _F	Output drop time (80% TO 20%)		0.32	0.8	ns
Transmission delay and output skew					
t _{PD}	Propagation delay		1.5	2	ns
t _{SK(O)}	output skew		9.2	50	ps
t _{PART-SKEW}	Part-to-part skew			400	ps

PHASE JITTER

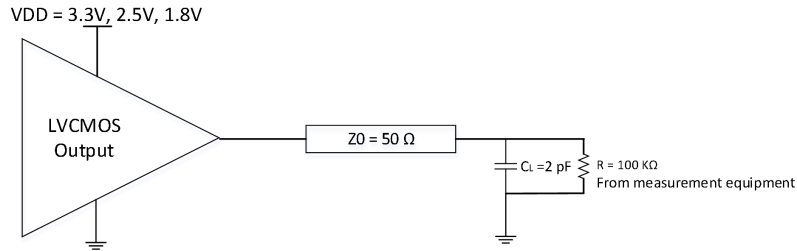


Jitter_156M25



Jitter_3V3_differential_Input

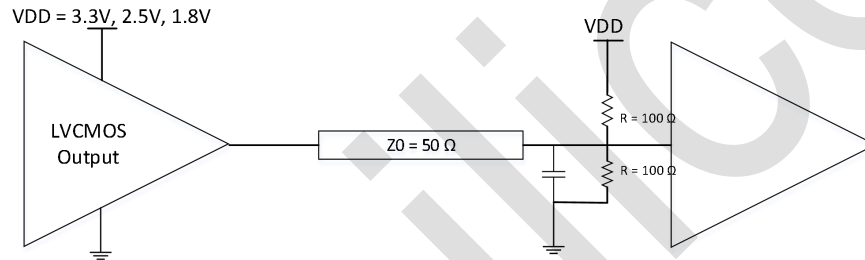
Parameter Measurement Information



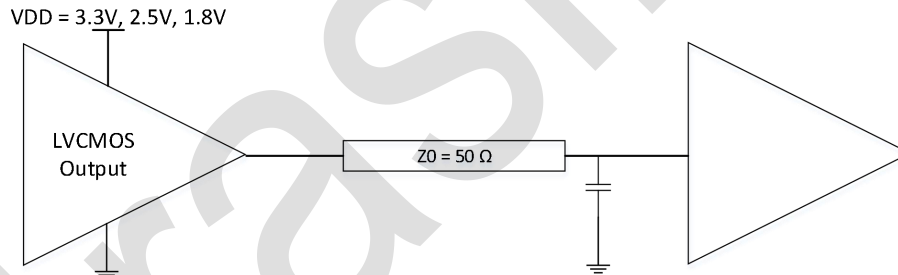
Test Load Circuit

Note:

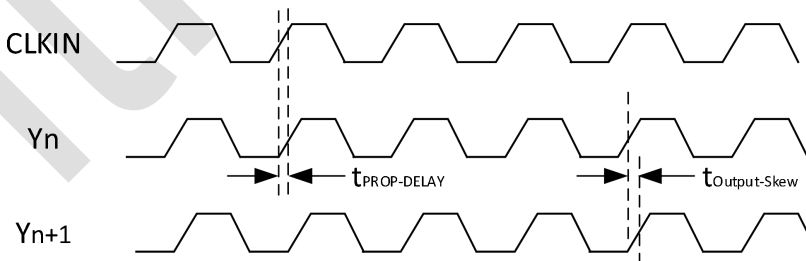
1. C_L include probe and jig capacitance.
2. All input pulses are supplied by generators having the following characteristics: Clock Frequency ≤ 250MHz, Z_o = 50 Ω, tr < 1.2ns, tf < 1.2ns



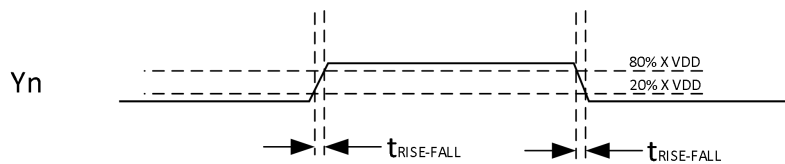
Application Load With 50-Ω Termination



Application Load With Termination

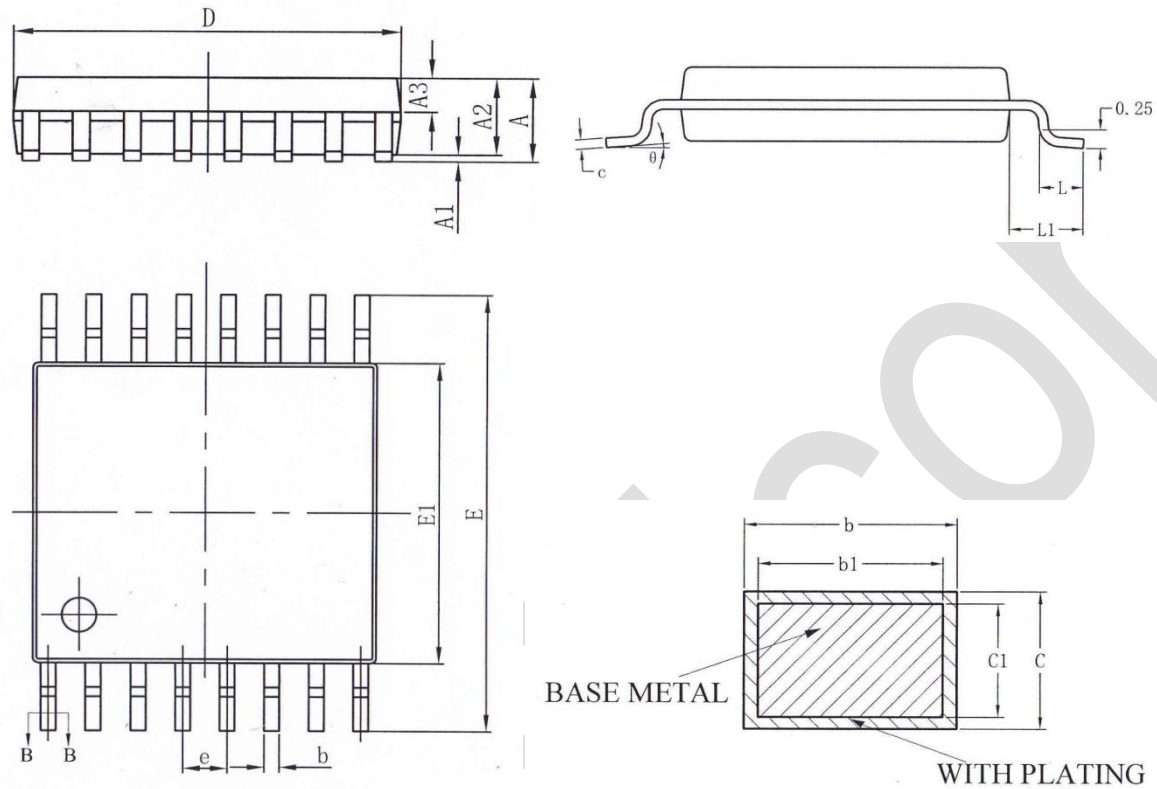


Propagation Delay t_{PROP-DELAY} and Output Skew t_{OUTPUT-SKEW}



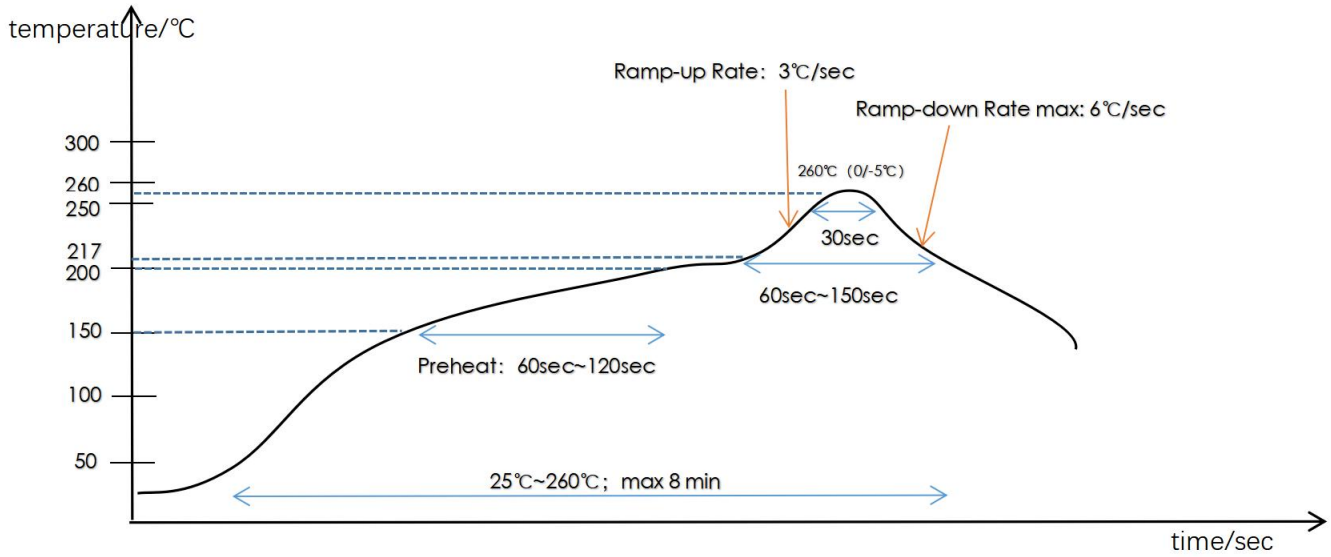
Rise and Fall Time t_{RISE-FALL}

PACKAGE DIMENSIONS



SYMBOL	Millimeter		
	Min	Nom	Max
A	-	-	1.20
A1	0.05	-	0.15
A2	0.90	1.00	1.05
A3	0.39	0.44	0.49
b	0.20	-	0.28
b1	0.19	0.22	0.25
c	0.13	-	0.17
c1	0.12	0.13	0.14
D	4.90	5.00	5.10
E1	4.30	4.40	4.50
E	6.20	6.40	6.60
e	0.65BSC		
L	0.45	0.60	0.75
L1	1.00REF		
θ	0	-	8°

Reflow profile



Recommended Temperature(PB-Free)

Reflow Condition	Convection or IR/Convection
Average ramp-up rate(217°C to Peak)	3°C/second max
Preheat temperature 175(±25)°C	60~120 seconds
Temperature maintained above 217°C	60~150 seconds
Time within 5°C of actual peak temperature	30 seconds
Peak temperature range	260 +0/-5°C
Ramp-down rate	6°C/second max
Time 25°C to peak temperature	8 minutes max
Maximum number of reflow cycles	≤3

Revision History

Date	Description of Change	Revision
2023.05.05	First Draft.	1.0

Ultrasilicon